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08/901,250

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970813	Serial No. 08/901,250
	Applicant(s): Y. INOUE et al.	
	Filing Date: August 29, 1997	Group Art Unit: 1763

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
gag	AA	6,071,807 ✓	Watanabe et al.	06/2000		
	AB	5,087,589 ✓	Chapman et al.	02/1992		
	AC	5,341,026 ✓	Harada et al.	08/1994		
	AD	5,514,910 ✓	Koyama	05/1996		
	AE	5,607,880 ✓	Suzuki et al.	03/1997		
	AF	5,702,568 ✓	Shin et al.	12/1997		
	AG	5,314,834 ✓	Mazure et al.	05/1994		
	AH	5,665,845 ✓	Allman	09/1997		
gag	AI					

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	Document No.	Date	Country	Translation (Yes or No)
gag	AJ AK	2-235358 ✓	09/18/90	Japan .
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AL	Wang et al., "A Study of Plasma Treatments on Siloxane SOB," IEEE VMIC Conference, June 7-8, 1994, pp. 101-107. ✓
AM	Chiang et al., "Defects Study on Spin on Glass Planarization Technology, IEEE VMIC Conference, June 15-16, 1987, pp. 404-412. ✓
AN	Lai-Juh Chen, et al., "Fluorine-Implanted Treatment (FIT) SOG for the Non-Etchback Intermetal Dielectric," IEEE VMIC Conference, June 7-8, 1994, pp. 81-86. ✓
AO	Moriya et al., "Modification Effects in Ion-Implanted SiO ₂ Spin-on-Glass," <u>J. Electrochem. Soc.</u> , Vol. 140, No. 5, May 1993, pp. 1442-1450. ✓
AP	Matsuura et al., "An Advanced Interlayer Dielectric System with Partially Converted Organic SOG Using Plasma Treatment," IEEE VMIC Conference, June 8-9, 1993, pp. 113-115. ✓
AQ	Ishida et al., "Mechanism for ALSiCu alloy Corrosion," <u>Jpn. J. Appl. Phys.</u> , Vol. 31 (1992), pp. 2045-2048. ✓
AR	Doki et al., "Moisture-Blocking Mechanism of ECR-Plasma," IEEE VMIC Conference, June 7-8, 1994, pp. 235-139. ✓
AS	Shimokawa et al., "Suppression of MOSFET hot carrier degradation by P-SiO underLayer," <u>The Institute of Electronics, Information and Communication Engineers</u> , Technical Report of IEICE, SDM92-133 (1992-12), pp. 89-94. ✓
AT	Murase et al., "Dielectric Constant of Silicon Dioxide Deposited by Atmospheric-Pressure Chemical Vapor Deposition Using Tetraethylorthosilicate and Ozone," <u>Jpn. J. Appl. Phys.</u> , Vol. 33 (1994), pp. 1385-1389. ✓

Examiner

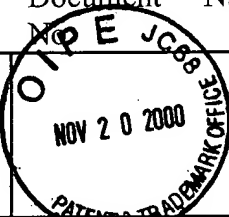
George Goudreau

Date Considered

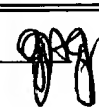
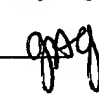
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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970813	Serial No. 09/921,250 ^{08,921,250}
	Applicant(s): Yasunori INOUE et al.	
	Filing Date: August 29, 1997	Group Art Unit: 1763

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OTHER DOCUMENTS

	AD	<u>LITHOGRAPHY 1: OPTICAL RESIST MATERIALS AND PROCESS TECHNOLOGY</u> , pp. 441.
	AE	SILICON PROCESSING FOR THE VLSI ERA - VOLUME II; 4.4.9.1 SOG Process Intefration, pp. 232. ✓
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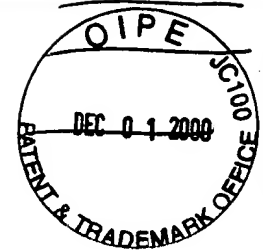
Examiner <u>George Goudreau</u> Date Considered <u>7-01-11</u>

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970813	Serial No. 09/921,250 ^{03/921,250}
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Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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	AB	5,404,046 ✓	Matsumoto et al.	04/95	257	750
<i>gag</i>	AC	5,898,221 ✓	Mizuhara et al.	04/99	257	751
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	AE					
	AF					



Examiner	Date Considered
<i>George Goudreau</i>	<i>7-011</i>

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